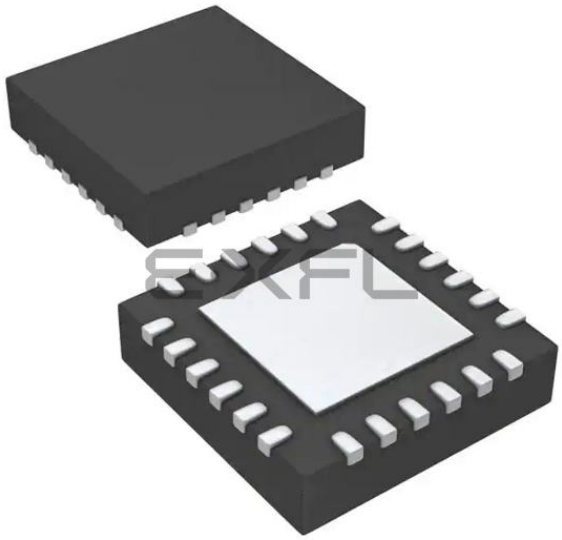
Renesas Electronics America Inc - R5F213G6MNNP#U0 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	19
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f213g6mnnp-u0

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

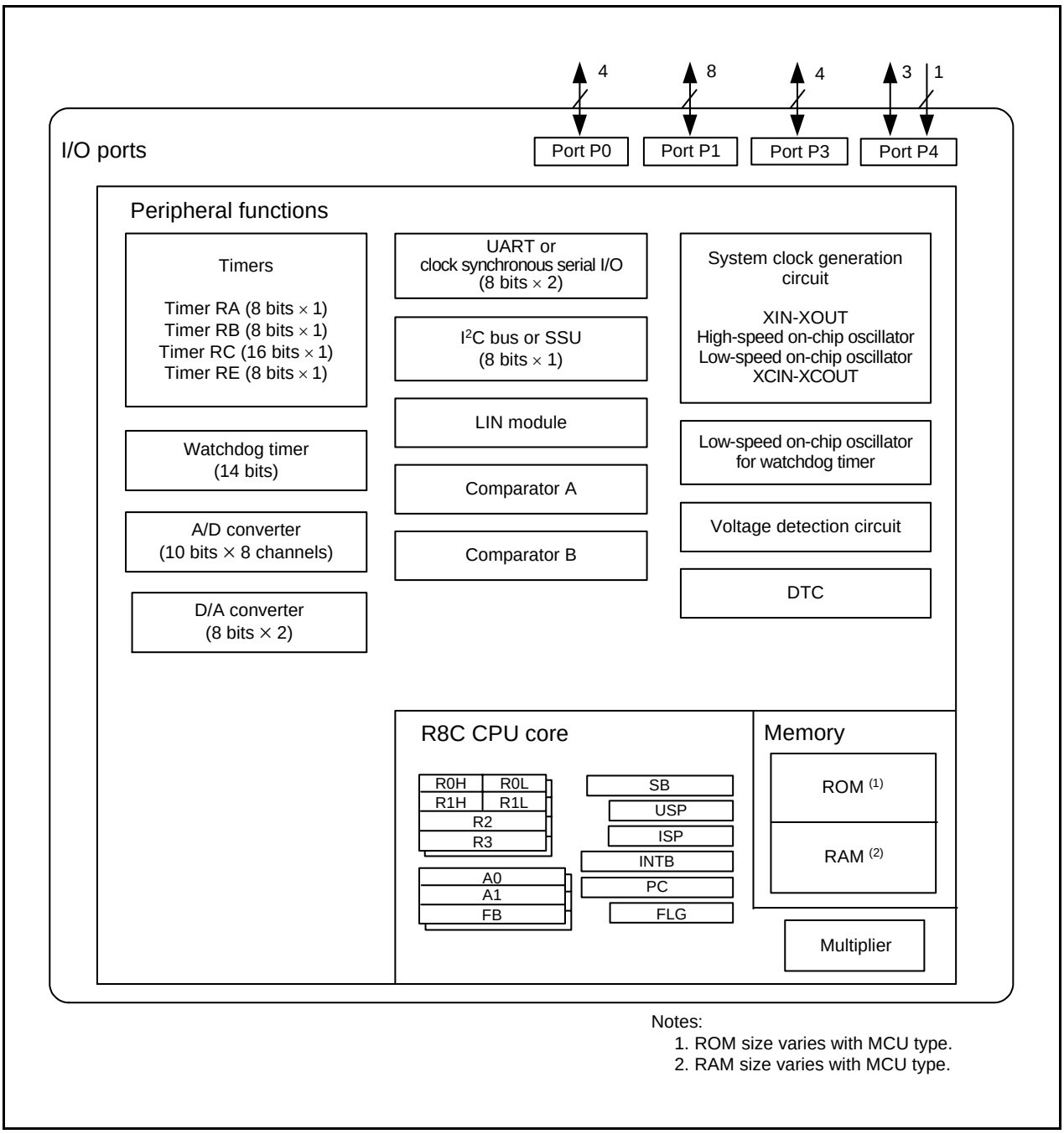
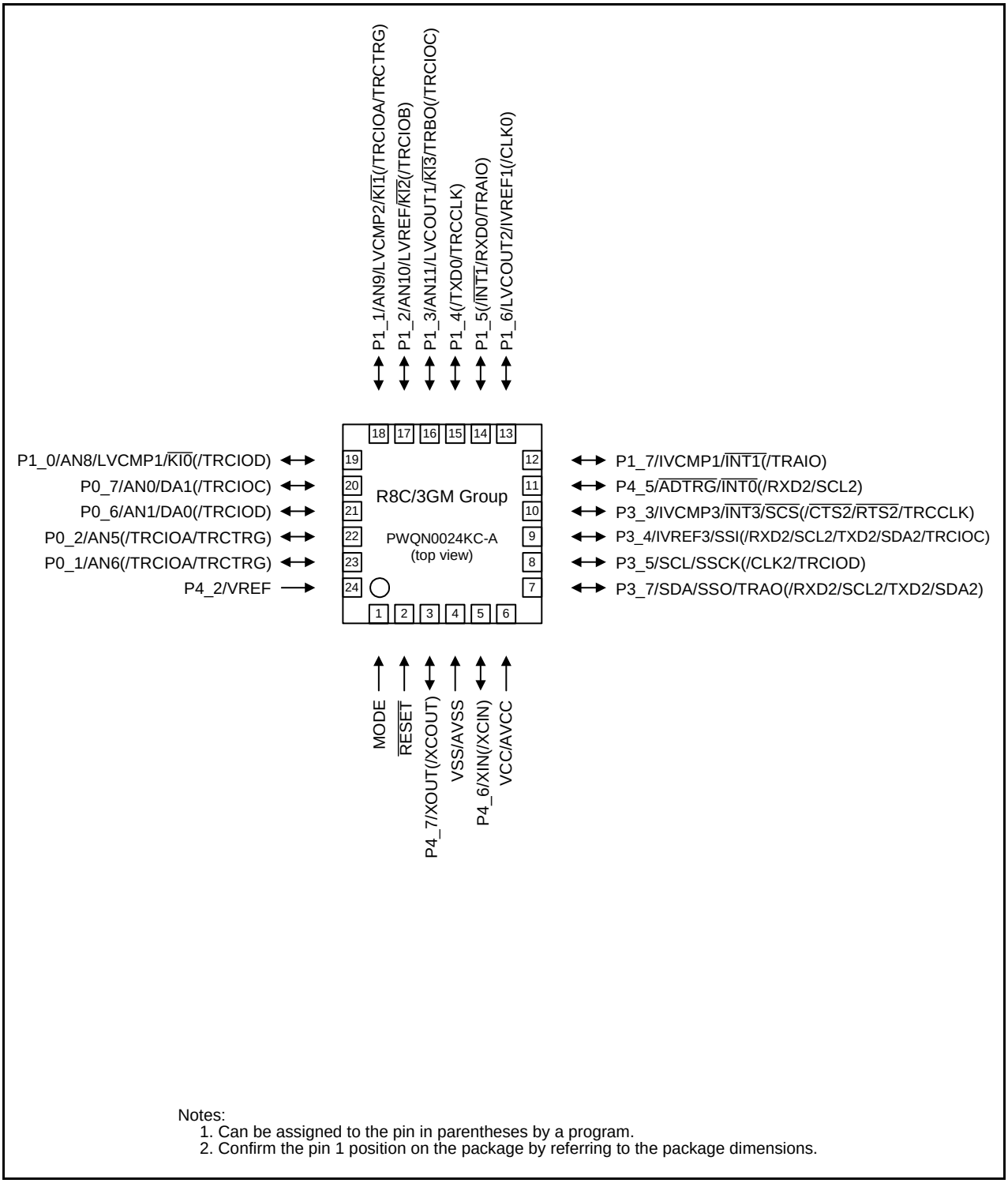


Figure 1.2 Block Diagram

1.4 Pin Assignment

Figure 1.3 shows Pin Assignment (Top View) of PWQN0024KC-A Package. Table 1.4 outlines the Pin Name Information by Pin Number.



Notes:
1. Can be assigned to the pin in parentheses by a program.
2. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.3 Pin Assignment (Top View) of PWQN0024KC-A Package

Table 1.4 Pin Name Information by Pin Number

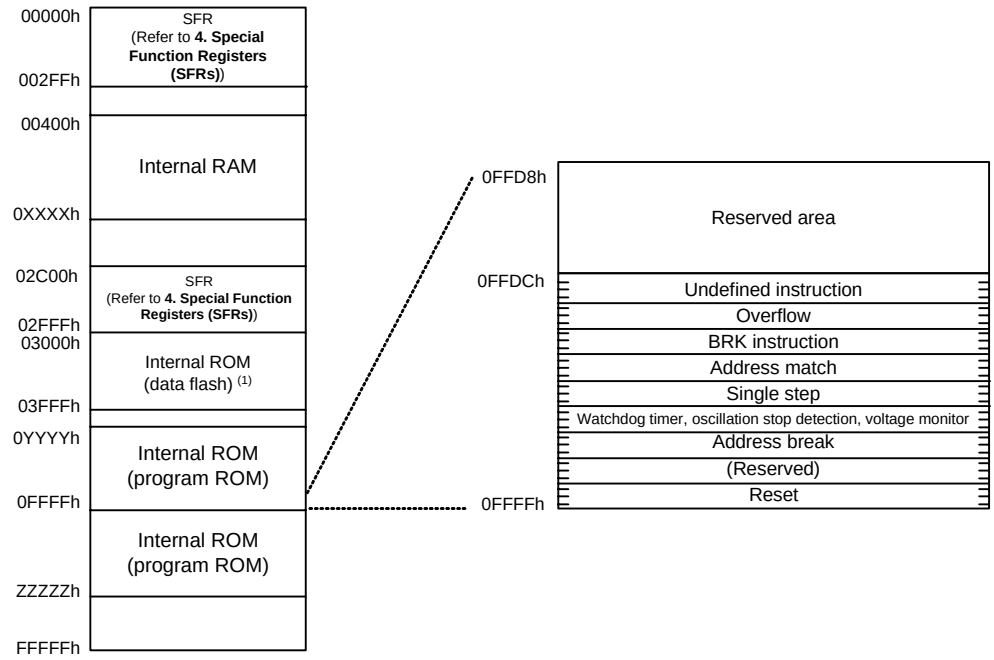
Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator A, Comparator B
1	MODE							
2	$\overline{\text{RESET}}$							
3	XOUT(/XCOUT)	P4_7						
4	VSS/AVSS							
5	XIN(/XCIN)	P4_6						
6	VCC/AVCC							
7		P3_7		TRAO	(RXD2/SCL2/ TXD2/SDA2)	SSO	SDA	
8		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
9		P3_4		(TRCIOC)	(RXD2/SCL2/ TXD2/SDA2)	SSI		IVREF3
10		P3_3	$\overline{\text{INT3}}$	(TRCCLK)	($\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$)	$\overline{\text{SCS}}$		IVCMP3
11		P4_5	$\overline{\text{INT0}}$		(RXD2/SCL2)			$\overline{\text{ADTRG}}$
12		P1_7	$\overline{\text{INT1}}$	(TRAIO)				IVCMP1
13		P1_6			(CLK0)			LVCOUT2/IVREF1
14		P1_5	($\overline{\text{INT1}}$)	(TRAIO)	(RXD0)			
15		P1_4		(TRCCLK)	(TXD0)			
16		P1_3	$\overline{\text{KI3}}$	TRBO/ (TRCIOC)				AN11/LVCOUT1
17		P1_2	$\overline{\text{KI2}}$	(TRCIOB)				AN10/LVREF
18		P1_1	$\overline{\text{KI1}}$	(TRCIOA/ TRCTRG)				AN9/LVCMP2
19		P1_0	$\overline{\text{KI0}}$	(TRCIOD)				AN8/LVCMP1
20		P0_7		(TRCIOC)				AN0/DA1
21		P0_6		(TRCIOD)				AN1/DA0
22		P0_2		(TRCIOA/ TRCTRG)				AN5
23		P0_1		(TRCIOA/ TRCTRG)				AN6
24		P4_2						VREF

Note:
1. Can be assigned to the pin in parentheses by a program.

3. Memory

3.1 R8C/3GM Group

Figure 3.1 is a Memory Map of R8C/3GM Group. The R8C/3GM Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 32-Kbyte internal ROM area is allocated addresses 08000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte) and block D (1 Kbyte).
2. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F213G2MNNP	8 Kbytes	0E000h	–	1 Kbyte	007FFh
R5F213G4MNNP	16 Kbytes	0C000h	–	1.5 Kbytes	009FFh
R5F213G5MNNP	24 Kbytes	0A000h	–	2 Kbytes	00BFFh
R5F213G6MNNP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh

Figure 3.1 Memory Map of R8C/3GM Group

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.12 list the special function registers. Table 4.13 lists the ID Code Areas and Option Function Select Area.

Table 4.1 SFR Information (1) (1)

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h
0006h	System Clock Control Register 0	CM0	00101000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Module Standby Control Register	MSTCR	00h
0009h	System Clock Control Register 3	CM3	00h
000Ah	Protect Register	PRCR	00h
000Bh	Reset Source Determination Register	RSTFR	0XXXXXXXb (2)
000Ch	Oscillation Stop Detection Register	OCD	00000100b
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTS	XXh
000Fh	Watchdog Timer Control Register	WDTC	00111111b
0010h			
0011h			
0012h			
0013h			
0014h			
0015h	High-Speed On-Chip Oscillator Control Register 7	FRA7	When shipping
0016h			
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b (3)
001Dh			
001Eh			
001Fh			
0020h			
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Control Register 1	FRA1	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h	On-Chip Reference Voltage Control Register	OCVREFCR	00h
0027h			
0028h	Clock Prescaler Reset Flag	CPSRF	00h
0029h	High-Speed On-Chip Oscillator Control Register 4	FRA4	When Shipping
002Ah	High-Speed On-Chip Oscillator Control Register 5	FRA5	When Shipping
002Bh	High-Speed On-Chip Oscillator Control Register 6	FRA6	When Shipping
002Ch			
002Dh			
002Eh			
002Fh	High-Speed On-Chip Oscillator Control Register 3	FRA3	When shipping
0030h	Voltage Monitor Circuit/Comparator A Control Register	CMPA	00h
0031h	Voltage Monitor Circuit Edge Select Register	VCAC	00h
0032h			
0033h	Voltage Detect Register 1	VCA1	00001000b
0034h	Voltage Detect Register 2	VCA2	00h (4) 00100000b (5)
0035h			
0036h	Voltage Detection 1 Level Select Register	VD1LS	00000111b
0037h			
0038h	Voltage Monitor 0 Circuit Control Register	VW0C	1100X010b (4) 1100X011b (5)
0039h	Voltage Monitor 1 Circuit Control Register	VW1C	10001010b

X: Undefined
Notes:
1. The blank areas are reserved and cannot be accessed by users.
2. The CWR bit in the RSTFR register is set to 0 after power-on and voltage monitor 0 reset. Hardware reset, software reset, or watchdog timer reset does not affect this bit.
3. The CSPROINI bit in the OFS register is set to 0.
4. The LVDAS bit in the OFS register is set to 1.
5. The LVDAS bit in the OFS register is set to 0.

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register (2)	SSUIC / IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h			
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1/Comparator A1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2/Comparator A2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:
1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.9 SFR Information (9) (1)

Address	Register	Symbol	After Reset
2C00h	DTC Transfer Vector Area		XXh
2C01h	DTC Transfer Vector Area		XXh
2C02h	DTC Transfer Vector Area		XXh
2C03h	DTC Transfer Vector Area		XXh
2C04h	DTC Transfer Vector Area		XXh
2C05h	DTC Transfer Vector Area		XXh
2C06h	DTC Transfer Vector Area		XXh
2C07h	DTC Transfer Vector Area		XXh
2C08h	DTC Transfer Vector Area		XXh
2C09h	DTC Transfer Vector Area		XXh
2C0Ah	DTC Transfer Vector Area		XXh
:	DTC Transfer Vector Area		XXh
:	DTC Transfer Vector Area		XXh
2C3Ah	DTC Transfer Vector Area		XXh
2C3Bh	DTC Transfer Vector Area		XXh
2C3Ch	DTC Transfer Vector Area		XXh
2C3Dh	DTC Transfer Vector Area		XXh
2C3Eh	DTC Transfer Vector Area		XXh
2C3Fh	DTC Transfer Vector Area		XXh
2C40h	DTC Control Data 0	DTCD0	XXh
2C41h			XXh
2C42h			XXh
2C43h			XXh
2C44h			XXh
2C45h			XXh
2C46h			XXh
2C47h			XXh
2C48h	DTC Control Data 1	DTCD1	XXh
2C49h			XXh
2C4Ah			XXh
2C4Bh			XXh
2C4Ch			XXh
2C4Dh			XXh
2C4Eh			XXh
2C4Fh			XXh
2C50h	DTC Control Data 2	DTCD2	XXh
2C51h			XXh
2C52h			XXh
2C53h			XXh
2C54h			XXh
2C55h			XXh
2C56h			XXh
2C57h			XXh
2C58h	DTC Control Data 3	DTCD3	XXh
2C59h			XXh
2C5Ah			XXh
2C5Bh			XXh
2C5Ch			XXh
2C5Dh			XXh
2C5Eh			XXh
2C5Fh			XXh
2C60h	DTC Control Data 4	DTCD4	XXh
2C61h			XXh
2C62h			XXh
2C63h			XXh
2C64h			XXh
2C65h			XXh
2C66h			XXh
2C67h			XXh
2C68h	DTC Control Data 5	DTCD5	XXh
2C69h			XXh
2C6Ah			XXh
2C6Bh			XXh
2C6Ch			XXh
2C6Dh			XXh
2C6Eh			XXh
2C6Fh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.11 SFR Information (11) (1)

Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h			XXh
2CB4h			XXh
2CB5h			XXh
2CB6h			XXh
2CB7h			XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h			XXh
2CBAh			XXh
2CBBh			XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h			XXh
2CC3h			XXh
2CC4h			XXh
2CC5h			XXh
2CC6h			XXh
2CC7h			XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h			XXh
2CCAh			XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h			XXh
2CD3h			XXh
2CD4h			XXh
2CD5h			XXh
2CD6h			XXh
2CD7h			XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h			XXh
2CDAh			XXh
2CDBh			XXh
2CDCh			XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h			XXh
2CE5h			XXh
2CE6h			XXh
2CE7h			XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h			XXh
2CEAh			XXh
2CEBh			XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	$-20°C \leq T_{opr} \leq 85°C$	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage					1.8	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage					–	0	–	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 V_{CC}	–	V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.5 V_{CC}	–	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.55 V_{CC}	–	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.65 V_{CC}	–	V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.65 V_{CC}	–	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.7 V_{CC}	–	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.8 V_{CC}	–	V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.85 V_{CC}	–	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.85 V_{CC}	–	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.85 V_{CC}	–	V_{CC}	V
		External clock input (XOUT)				1.2	–	V_{CC}	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	–	0.2 V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	–	0.2 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	–	0.2 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	–	0.2 V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	–	0.4 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	–	0.3 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	–	0.2 V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	–	0.55 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	–	0.45 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	–	0.35 V_{CC}	V
		External clock input (XOUT)				0	–	0.4	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				–	–	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				–	–	–80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				–	–	–10	mA
		Drive capacity High				–	–	–40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				–	–	–5	mA
		Drive capacity High				–	–	–20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				–	–	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				–	–	10	mA
		Drive capacity High				–	–	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				–	–	5	mA
		Drive capacity High				–	–	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	–	–	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency				1.8 V ≤ V_{CC} ≤ 5.5 V	–	32.768	50	kHz
fOCO40M	When used as the count source for timer RC (3)				2.7 V ≤ V_{CC} ≤ 5.5 V	32	–	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	–	–	5	MHz
–	System clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	–	–	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	–	–	5	MHz

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC in the range of V_{CC} = 2.7 V to 5.5V.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0, AN1, AN5, AN6 input, AN8 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
I_{Vref}	V_{ref} current		V_{CC} = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
V_{ref}	Reference voltage				2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	–	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.8 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		10,000 (3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20	–	85	°C
–	Data hold time (7)	Ambient temperature = 55 °C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

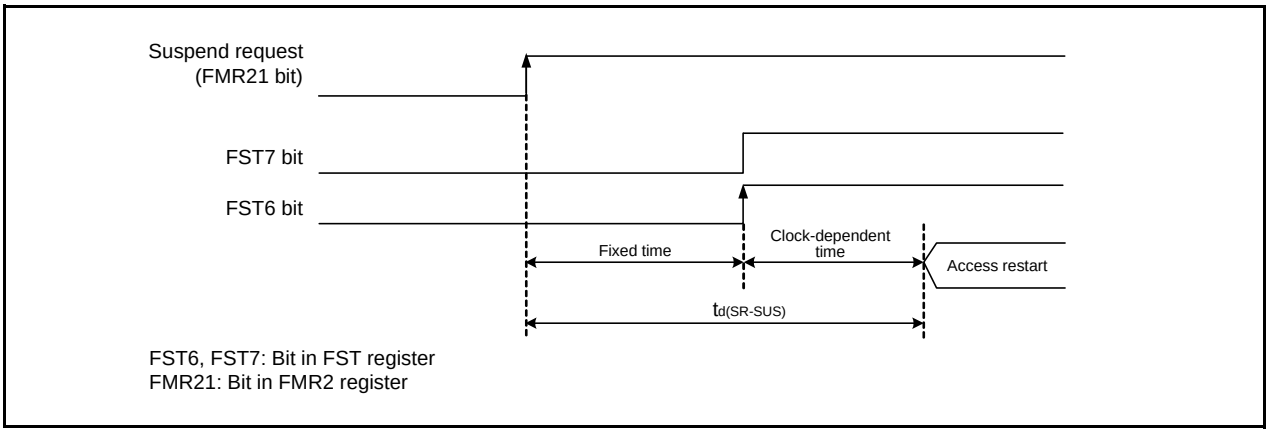


Figure 5.2 Time delay until Suspend

Table 5.13 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	39.2	40	40.8	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	39.6	40	40.4	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	36.126	36.864	37.602	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	39.495	36.864	37.233	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V –20°C ≤ T_{opr} ≤ 85°C	31.36	32	32.64	MHz
		V_{CC} = 1.8 V to 5.5 V T_{opr} = 25°C	31.68	32	32.32	MHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	100	450	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	500	–	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.14 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA
fOCO-WDT	Low-speed on-chip oscillator frequency for the watchdog timer		60	125	250	kHz
–	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25°C	–	30	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	2	–	µA

Note:
1. V_{CC} = 1.8 to 5.5 V, T_{opr} = –20 to 85°C (N version), unless otherwise specified.

Table 5.15 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		–	–	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.16 Timing Requirements of Synchronous Serial Communication Unit (SSU) (1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC} (2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		1t_{CYC} + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		1t_{CYC} + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version), unless otherwise specified.
2. 1t_{CYC} = 1/f1(s)

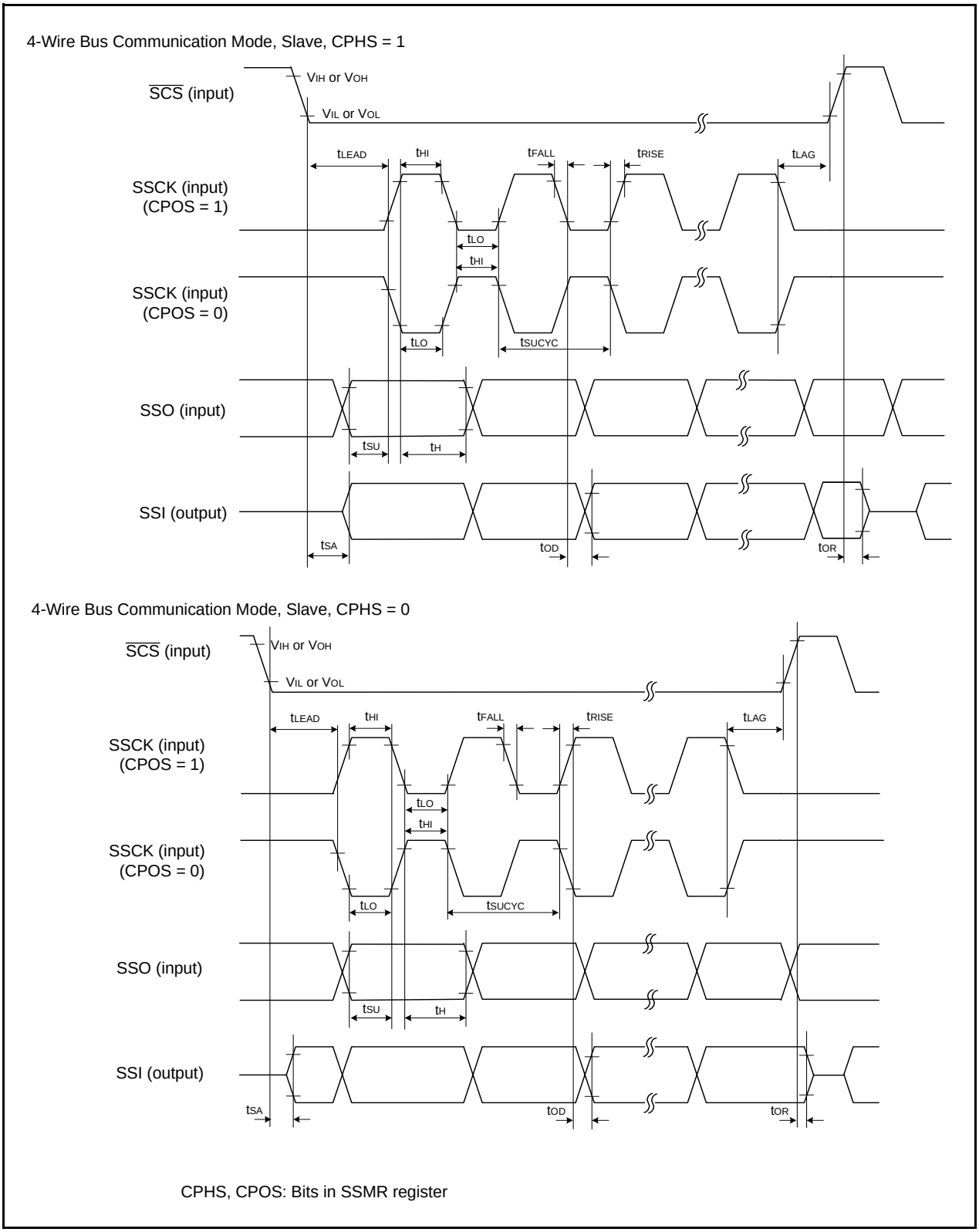


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

Table 5.22 Serial Interface

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	When external clock is selected	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width		100	–	ns
$t_{W(CKL)}$	CLKi input “L” width		100	–	ns
$t_{d(C-Q)}$	TXDi output delay time		–	90	ns
$t_{h(C-Q)}$	TXDi hold time		0	–	ns
$t_{su(D-C)}$	RXDi input setup time		10	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns
$t_{d(C-Q)}$	TXDi output delay time	When internal clock is selected	–	10	ns
$t_{su(D-C)}$	RXDi input setup time		90	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns

i = 0 or 2

Note:

1. 1. Vcc = 5 V and Topr = –20 to 85°C (N version), unless otherwise specified.

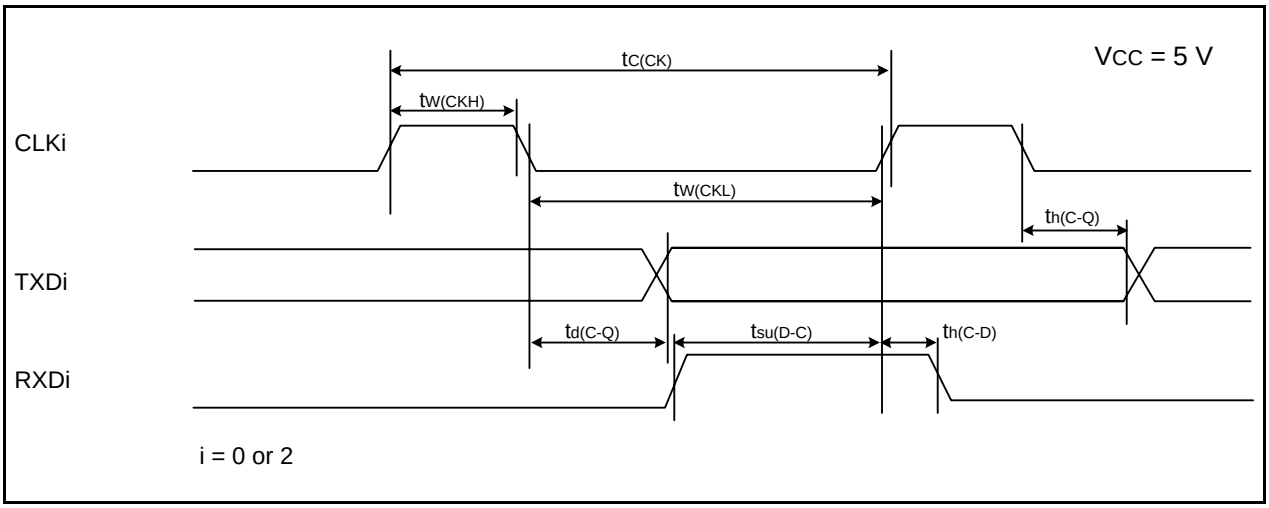


Figure 5.10 Serial Interface Timing Diagram when Vcc = 5 V

Table 5.23 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	–	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

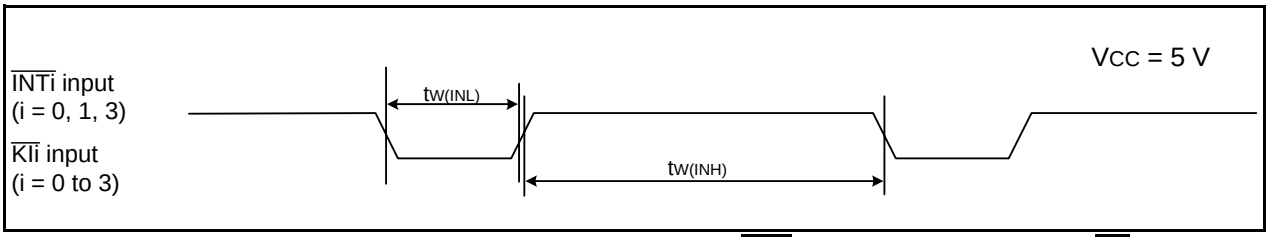


Figure 5.11 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 5 V

Table 5.25 Electrical Characteristics (4) [2.7 V ≤ Vcc < 3.3 V]
(Topr = –20 to 85°C (N version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
ICC	Power supply current (VCC = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are VSS	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4.0	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16 MSTIIC = MSTTRD = MSTTRC = 1	–	1	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	–	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, FMR27 = 1, VCA20 = 0	–	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division, Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	–	40	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	–	3.5	–	µA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	2.0	5.0	µA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	5.0	–	µA

Table 5.28 Serial Interface

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	When external clock is selected	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width		150	–	ns
$t_{W(CKL)}$	CLKi Input “L” width		150	–	ns
$t_{d(C-Q)}$	TXDi output delay time		–	120	ns
$t_{h(C-Q)}$	TXDi hold time		0	–	ns
$t_{su(D-C)}$	RXDi input setup time		30	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns
$t_{d(C-Q)}$	TXDi output delay time	When internal clock is selected	–	30	ns
$t_{su(D-C)}$	RXDi input setup time		120	–	ns
$t_{h(C-D)}$	RXDi input hold time		90	–	ns

i = 0 or 2

Note:

1. Vcc = 3 V and Topr = –20 to 85°C (N version), unless otherwise specified.

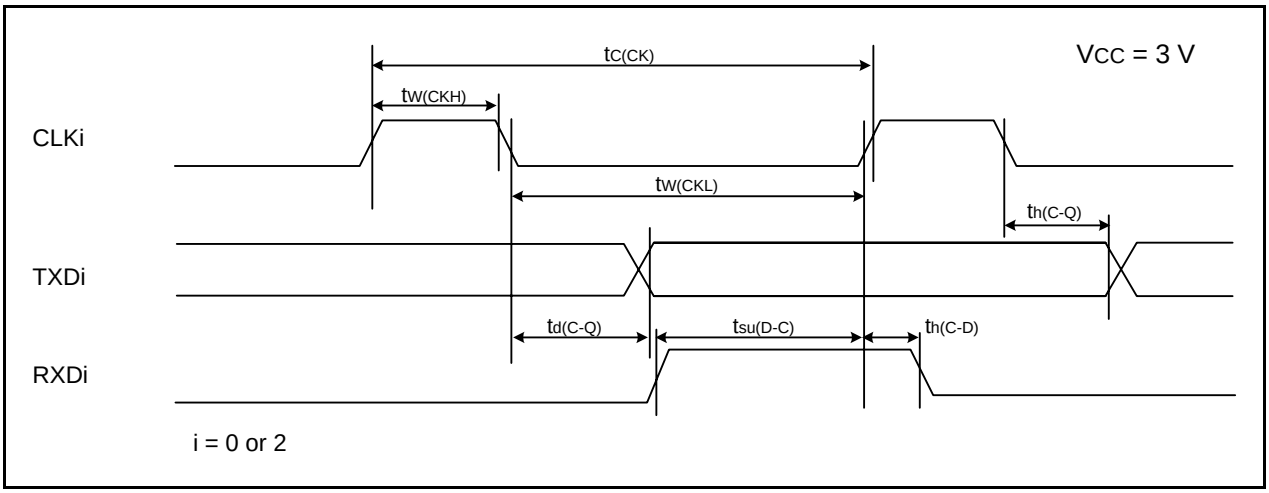


Figure 5.14 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.29 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	380 (1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	380 (2)	–	ns

Notes:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

Figure 5.15 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 3 V

Table 5.30 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 2.2 V		0.05	0.2	–	V
		$\overline{RESET}$	V_{CC} = 2.2 V		0.05	0.20	–	V
I_{IH}	Input “H” current		VI = 2.2 V, V_{CC} = 2.2 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 2.2 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V and T_{opr} = –20 to 85°C (N version), f(XIN) = 5 MHz, unless otherwise specified.

Timing Requirements
(Unless Otherwise Specified: Vcc = 2.2 V, Vss = 0 V at Topr = 25°C)

Table 5.32 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	200	–	ns
$t_{WH(XOUT)}$	XOUT input “H” width	90	–	ns
$t_{WL(XOUT)}$	XOUT input “L” width	90	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	µs

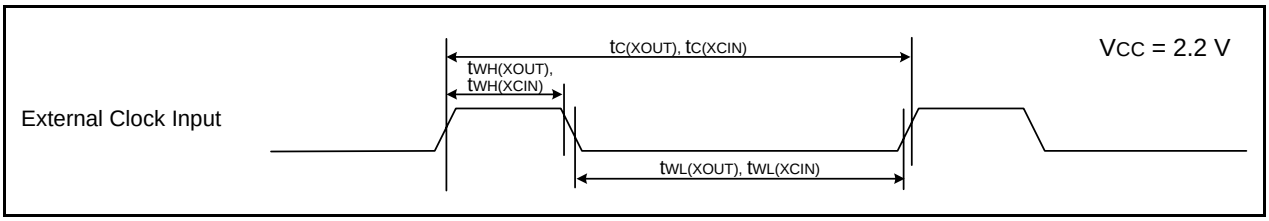


Figure 5.16 External Clock Input Timing Diagram when Vcc = 2.2 V

Table 5.33 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

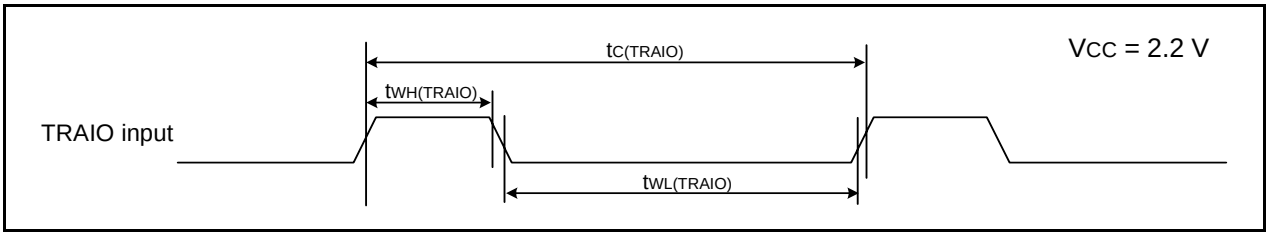


Figure 5.17 TRAIO Input Timing Diagram when Vcc = 2.2 V